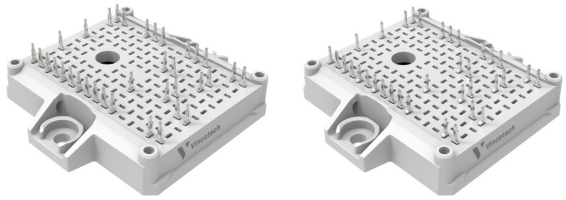
10-EY12PMA025M7-L187A78T
10-E212PMA025M7-L187A78Z
datasheet

***flow*PIM E2** | **1200 V / 25 A**

Features

- IGBT M7 with low V_{CEsat} and improved EMC behavior
- Standard industrial housing
- Optimized $R_{th(j-s)}$ with Phase Change Material
- Built-in NTC

flow E2 12 mm housing

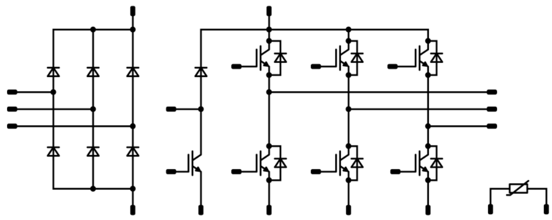


Press-fit pin Solder pin

Target applications

- Industrial Drives

Schematic



Types

- 10-EY12PMA025M7-L187A78T
- 10-E212PMA025M7-L187A78Z

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition			Value	Unit
Inverter Switch						
Collector-emitter voltage	V_{CES}				1200	V
Collector current	I_C	$T_j = T_{jmax}$		T_s = 80 °C	33	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}			50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$		T_s = 80 °C	79	W
Gate-emitter voltage	V_{GES}				±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V	V_{cc} = 800 V	T_j =150 °C	9,5	µs
Maximum junction temperature	T_{jmax}				175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition			Value	Unit
Inverter Diode						
Peak repetitive reverse voltage	V_{RRM}				1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$		T_s = 80 °C	35	A
Repetitive peak forward current	I_{FRM}	T_j limited by T_{jmax}			50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$		T_s = 80 °C	71	W
Maximum junction temperature	T_{jmax}				175	°C
Brake Switch						
Collector-emitter voltage	V_{CES}				1200	V
Collector current	I_C	$T_j = T_{jmax}$		T_s = 80 °C	33	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}			50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$		T_s = 80 °C	79	W
Gate-emitter voltage	V_{GES}				±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V	V_{cc} = 800 V	T_j =150 °C	9,5	μs
Maximum junction temperature	T_{jmax}				175	°C
Brake Diode						
Peak repetitive reverse voltage	V_{RRM}				1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$		T_s = 80 °C	14	A
Repetitive peak forward current	I_{FRM}	T_j limited by T_{jmax}			20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$		T_s = 80 °C	43	W
Maximum junction temperature	T_{jmax}				175	°C
Rectifier Diode						
Peak repetitive reverse voltage	V_{RRM}				1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$		T_s = 80 °C	51	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave t_p = 10 ms		T_j = 150 °C	350	A
Surge current capability	I^2t				610	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$		T_s = 80 °C	60	W
Maximum junction temperature	T_{jmax}				150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
		AC Voltage	t_p = 1 min	2500	V
Creepage distance				min. 12,7	mm
Clearance		Press-fit pin / Solder pin		8,83 / 8,85	mm
Comparative Tracking Index	CTI			≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0025	25	5,4	6,0	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150		1,65 1,89 1,95	2,15	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			70	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}							4800		
Output capacitance	C_{oes}		0	10		25		170		pF
Reverse transfer capacitance	C_{res}							57		
Gate charge	Q_g		15	600	25	25		180		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,20		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$					25 125 150		147 149 145		
Rise time	t_r	R_{gon} = 16 Ω R_{goff} = 16 Ω				25 125 150		29 33 34		
Turn-off delay time	$t_{d(off)}$					25 125 150		171 191 196		ns
Fall time	t_f		±15	600	25	25 125 150		95 110 115		
Turn-on energy (per pulse)*	E_{on}	Q_{rFWD} = 2,5 µC Q_{rFWD} = 3,9 µC Q_{rFWD} = 4,3 µC				25 125 150		2,06 2,66 2,82		mWs
Turn-off energy (per pulse)*	E_{off}					25 125 150		1,67 2,18 2,29		

* Ls = 10 nH

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				25	25 125 150		1,63 1,70 1,69	2,1	V
Reverse leakage current	I_R			1200		25			35	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,34		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 645 A/µs di/dt = 673 A/µs di/dt = 633 A/µs	±15	600	25	25 125 150		21 23 23		A
Reverse recovery time	t_{rr}					25 125 150		254 367 404		ns
Recovered charge	Q_r					25 125 150		2,54 3,88 4,28		µC
Reverse recovered energy	E_{rec}					25 125 150		0,884 1,45 1,61		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		217 134 132		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0025	25	5,4	6,0	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150		1,65 1,89 1,95	2,15	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			70	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}							4800		
Output capacitance	C_{oes}		0	10		25		170		pF
Reverse transfer capacitance	C_{res}							57		
Gate charge	Q_g		15	600	25	25		180		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,20		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$					25 125 150		403 389 382		
Rise time	t_r	R_{gon} = 32 Ω R_{goff} = 32 Ω				25 125 150		109 117 120		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		208 233 240		
Fall time	t_f		±15	600	25	25 125 150		81 93 96		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 1,5 µC Q_{rFWD} = 2,3 µC Q_{rFWD} = 2,6 µC				25 125 150		3,05 3,62 3,79		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,67 2,23 2,39		

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				10	25 125 150		1,61 1,69 1,69	2,1	V
Reverse leakage current	I_R			1200		25			25	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,19		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 207 A/µs di/dt = 210 A/µs di/dt = 196 A/µs	±15	600	25	25 125 150		9 10 10		A
Reverse recovery time	t_{rr}					25 125 150		317 448 499		ns
Recovered charge	Q_r					25 125 150		1,54 2,34 2,61		µC
Reverse recovered energy	E_{rec}					25 125 150		0,518 0,867 0,980		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		52 38 38		A/µs
Rectifier Diode										
Static										
Forward voltage	V_F				45	25 125		1,15 1,12		V
Reverse leakage current	I_R			1600		25 150			50	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,17		K/W

Characteristic Values

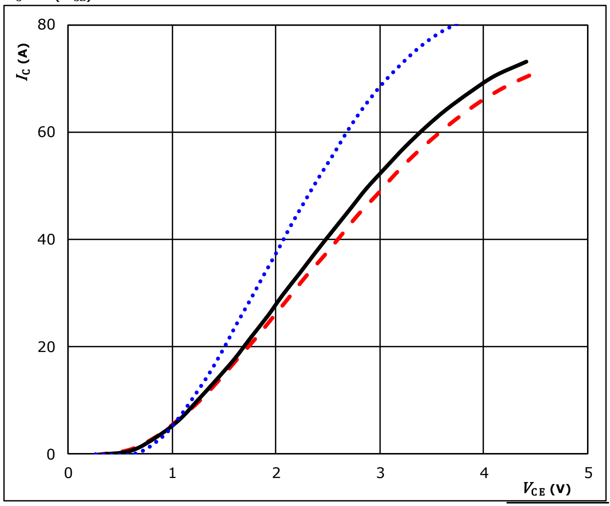
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Rated resistance	R					25		5		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 493 Ω				100	-5		+5	%
Power dissipation	P					25		245		mW
Power dissipation constant						25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. ±2 %				25		3375		K
B-value	$B_{(25/100)}$	Tol. ±2 %				25		3437		K
Vincotech NTC Reference									K	

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

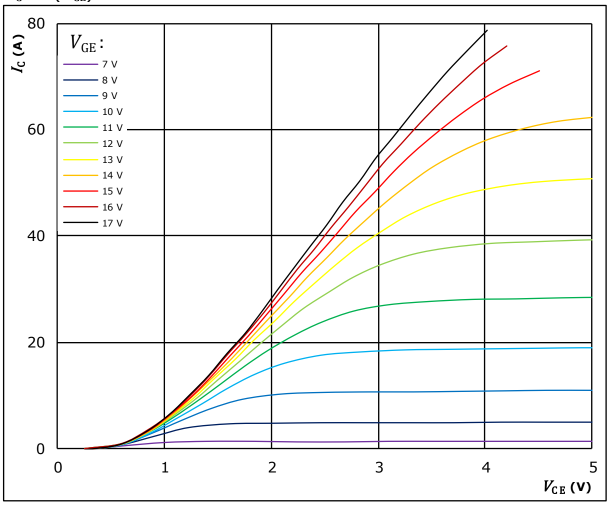


t_p =	250	µs		25 °C	dotted
V_{GE} =	15	V	T_j:	125 °C	solid
				150 °C	dashed

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



t_p = 250 µs

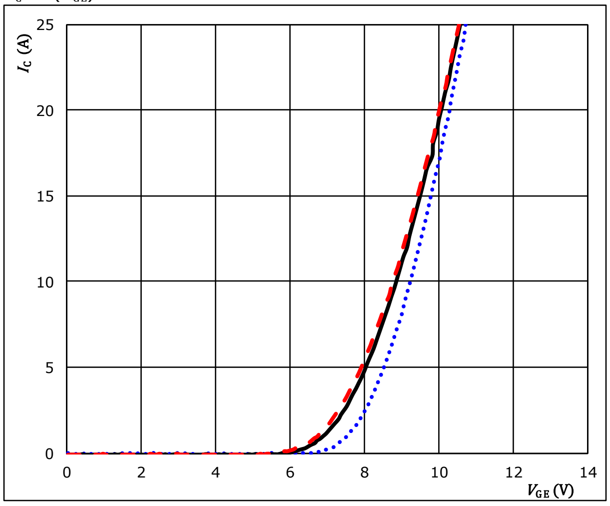
T_j = 125 °C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

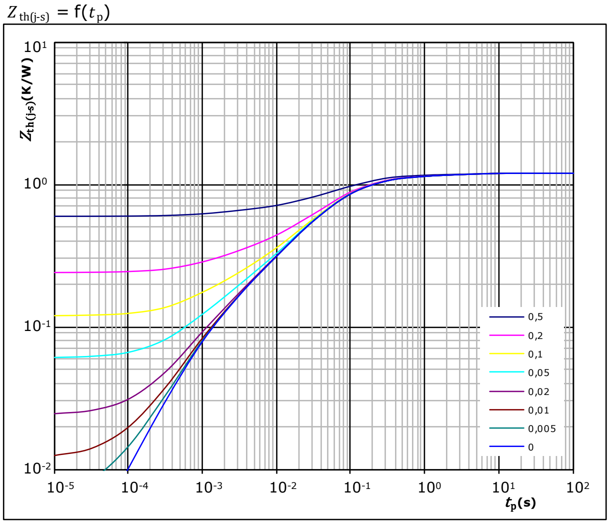


t_p =	100	µs		25 °C	dotted
V_{CE} =	10	V	T_j:	125 °C	solid
				150 °C	dashed

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,20 K/W

IGBT thermal model values

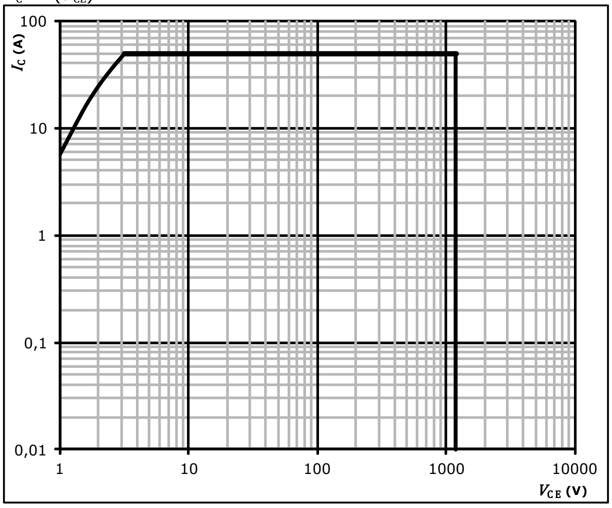
R (K/W)	τ (s)
7,19E-02	2,96E+00
1,76E-01	3,16E-01
6,46E-01	6,48E-02
2,16E-01	1,08E-02
8,54E-02	1,15E-03

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



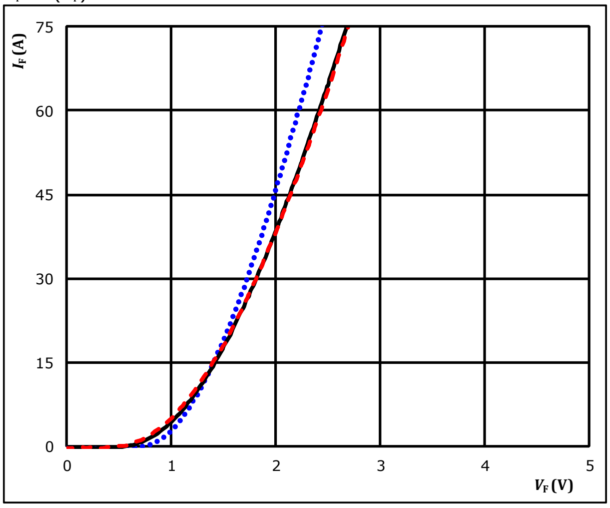
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



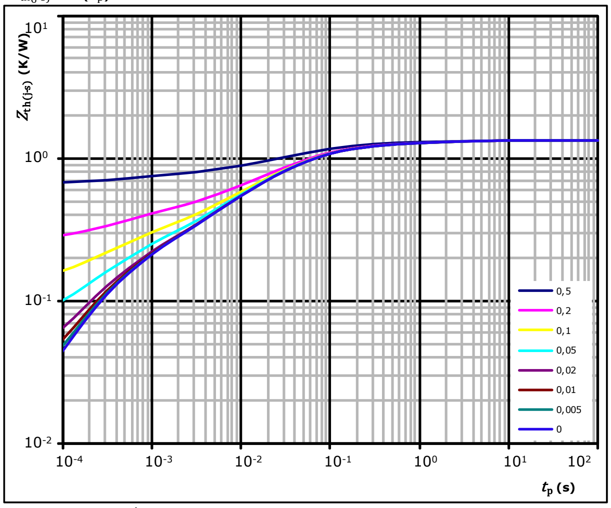
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,34 K/W

FWD thermal model values

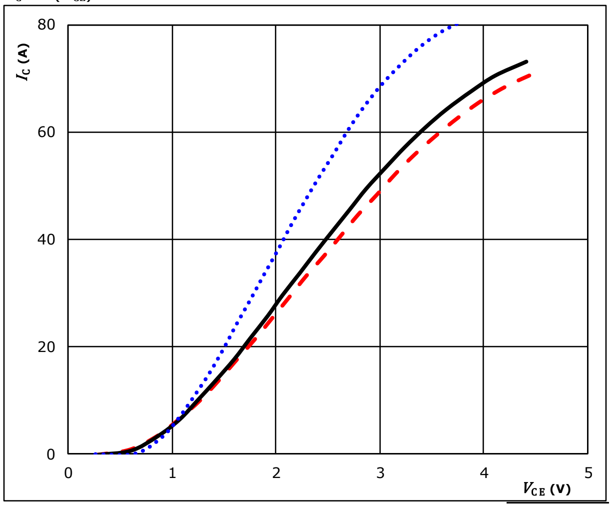
R (K/W)	τ (s)
7,90E-02	2,29E+00
1,38E-01	2,89E-01
5,15E-01	5,53E-02
3,34E-01	1,22E-02
1,30E-01	2,48E-03
1,40E-01	3,42E-04

Brake Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

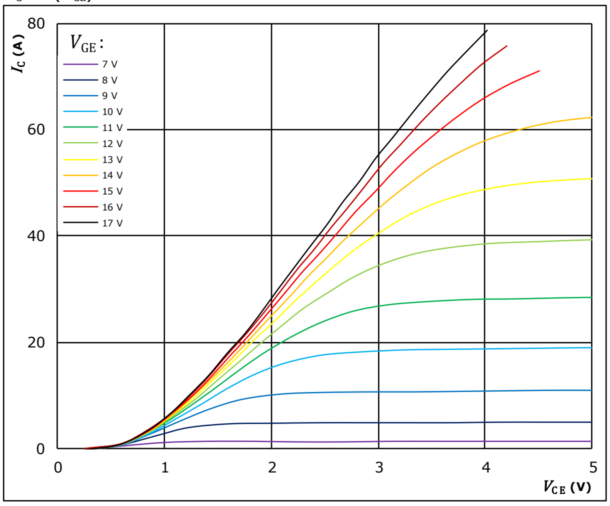


t_p =	250	µs		25 °C	
V_{GE} =	15	V	T_j:	125 °C	
				150 °C	

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



t_p = 250 µs

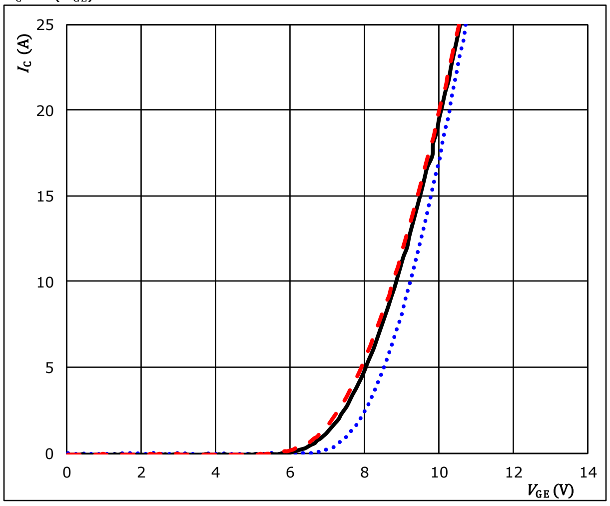
T_j = 125 °C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

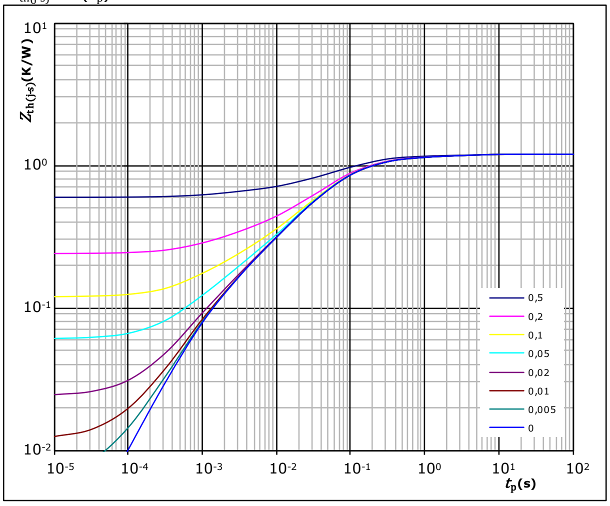


t_p =	100	µs		25 °C	
V_{CE} =	10	V	T_j:	125 °C	
				150 °C	

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,20 K/W

IGBT thermal model values

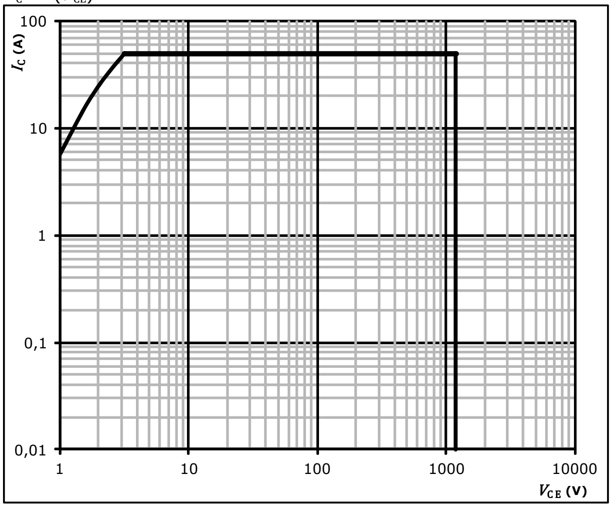
R (K/W)	τ (s)
7,19E-02	2,96E+00
1,76E-01	3,16E-01
6,46E-01	6,48E-02
2,16E-01	1,08E-02
8,54E-02	1,15E-03

Brake Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



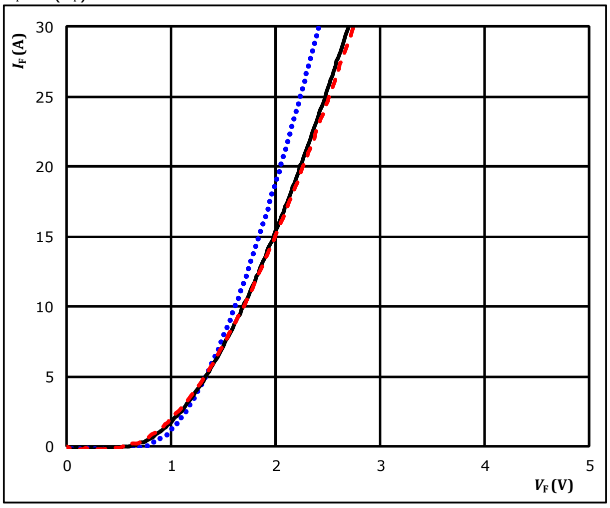
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Brake Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



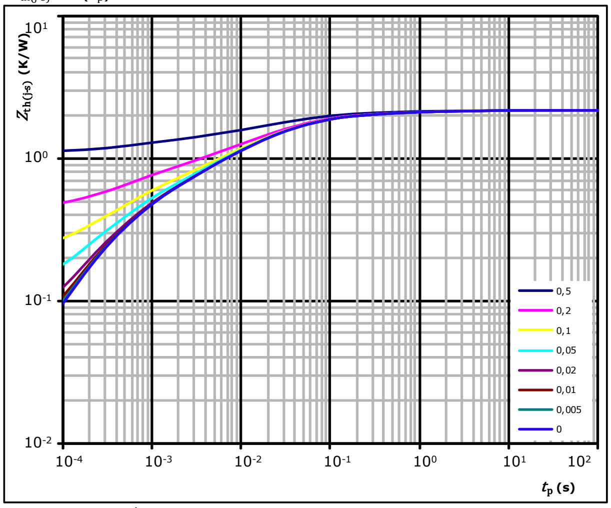
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,19 K/W

FWD thermal model values

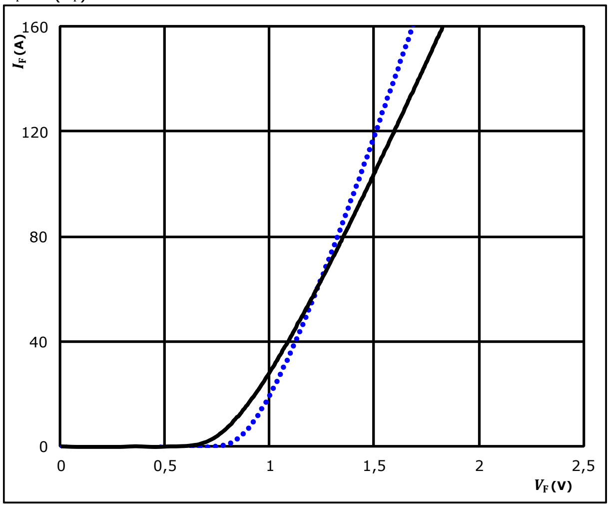
R (K/W)	τ (s)
8,09E-02	3,20E+00
2,08E-01	2,82E-01
6,85E-01	4,41E-02
5,92E-01	1,02E-02
3,27E-01	2,02E-03
2,95E-01	3,64E-04

Rectifier Diode Characteristics

figure 1. **Rectifier Diode**

Typical forward characteristics

$I_F = f(V_F)$



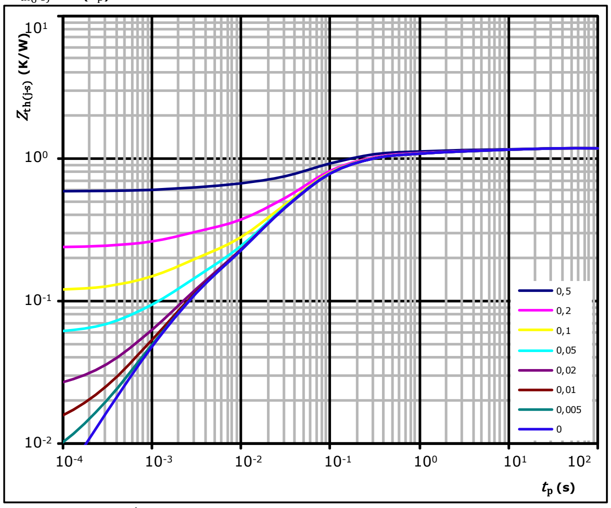
t_p = 250 µs

T_j: 25 °C (dotted), 125 °C (solid)

figure 2. **Rectifier Diode**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,17 K/W

Diode thermal model values

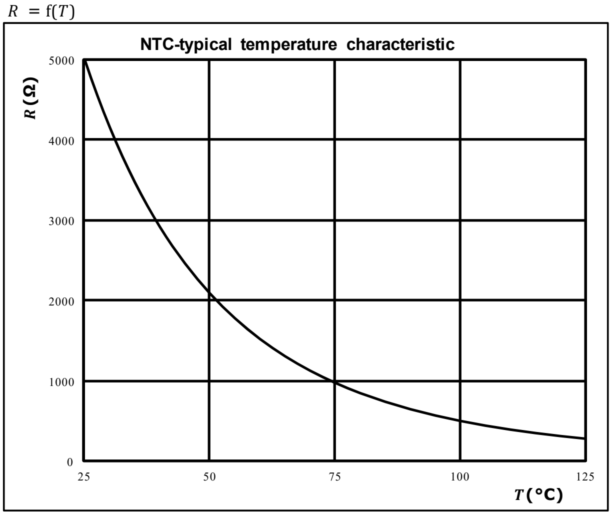
R (K/W)	τ (s)
7,71E-02	9,00E+00
1,19E-01	7,09E-01
4,99E-01	1,03E-01
3,97E-01	3,61E-02
8,19E-02	2,07E-03

Thermistor Characteristics

figure 1. **Thermistor**

Typical NTC characteristic as a function of temperature

$R = f(T)$

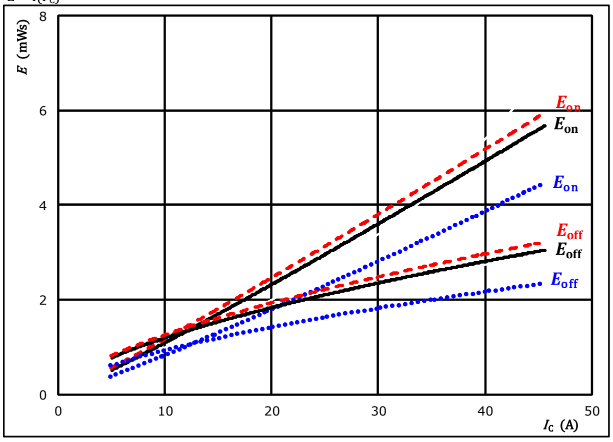


Inverter Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



With an inductive load at

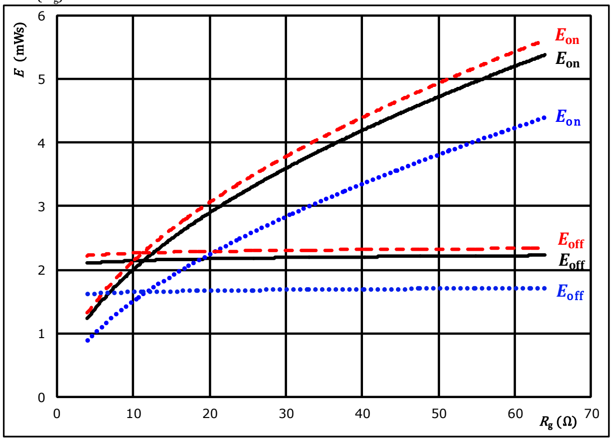
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 16 Ω
R_{goff} = 16 Ω

T_j: 25 °C; 125 °C; 150 °C

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



With an inductive load at

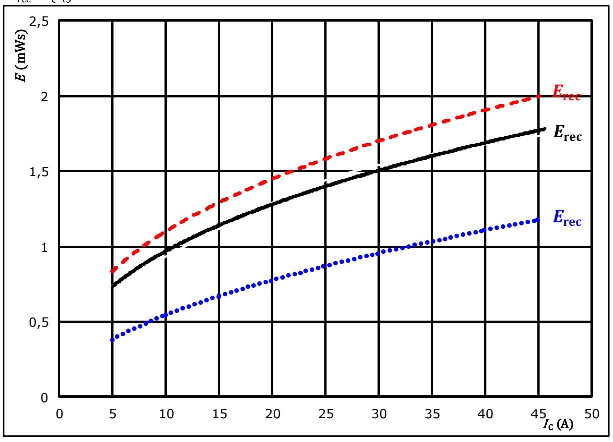
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 25 A

T_j: 25 °C; 125 °C; 150 °C

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_c)$



With an inductive load at

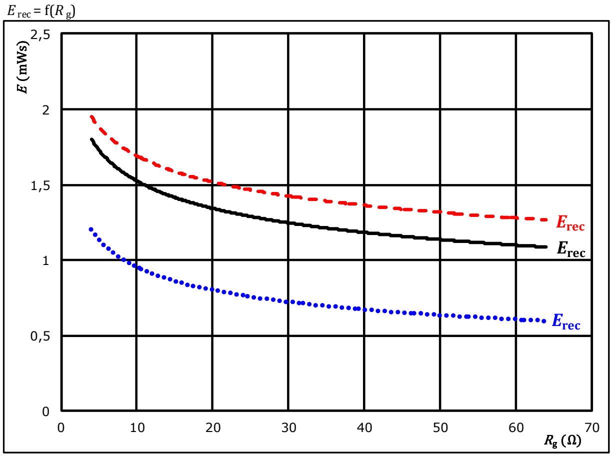
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 16 Ω

T_j: 25 °C; 125 °C; 150 °C

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 25 A

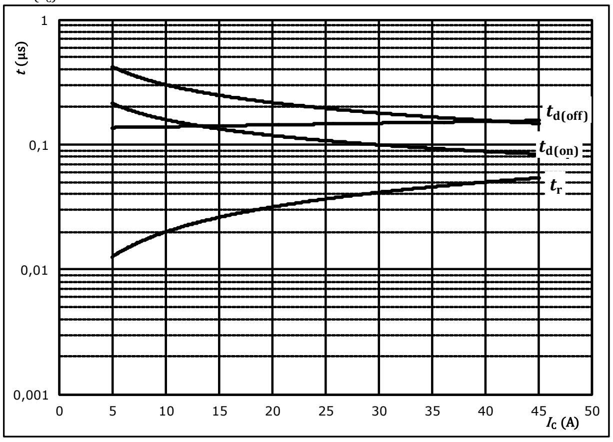
T_j: 25 °C; 125 °C; 150 °C

Inverter Switching Characteristics

figure 5. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



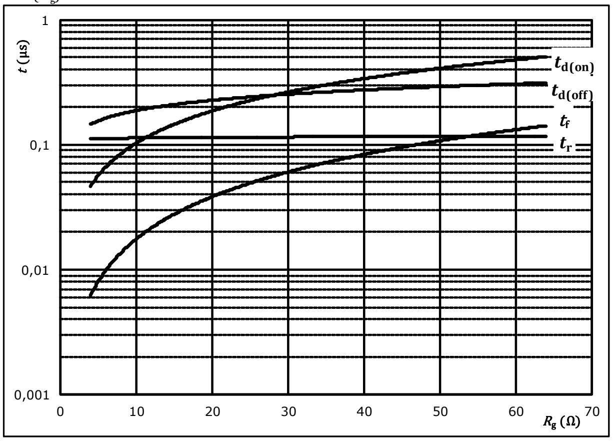
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 6. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



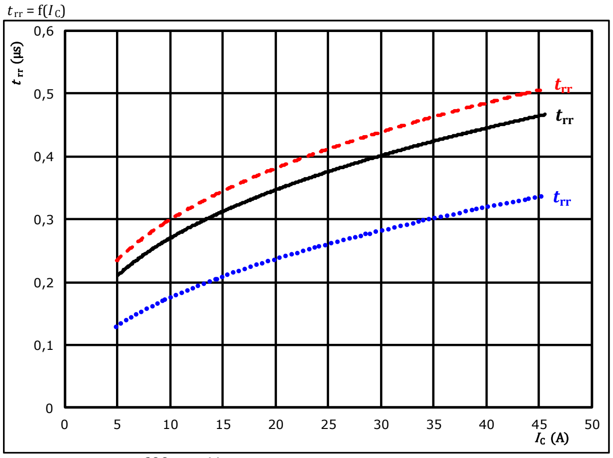
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

figure 7. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

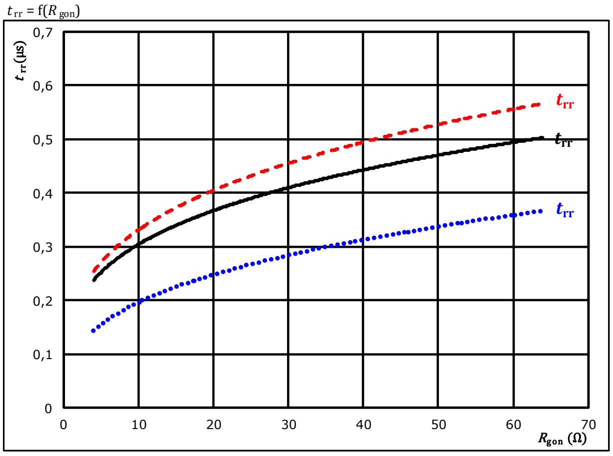


At						
V_{CE} =	600	V		25 °C	···········
V_{GE} =	±15	V	T_j:	125 °C	———
R_{gon} =	16	Ω		150 °C	– – –

figure 8. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



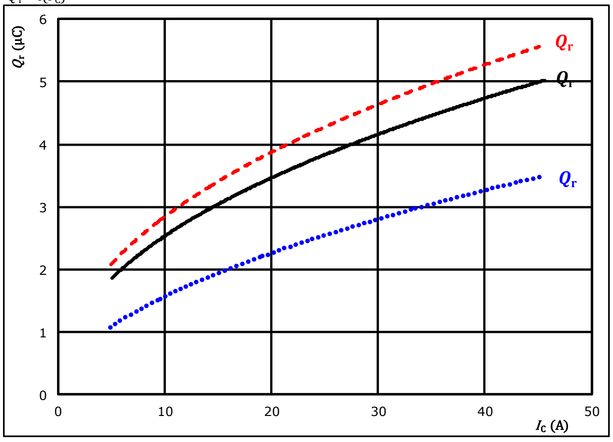
At						
V_{CE} =	600	V		25 °C	···········
V_{GE} =	±15	V	T_j:	125 °C	———
I_C =	25	A		150 °C	– – –

Inverter Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

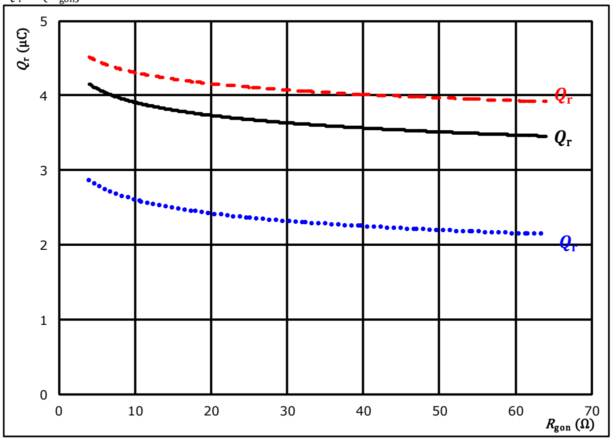


At					
V_{CE} =	600	V		25 °C	
V_{GE} =	±15	V	T_j:	125 °C	
R_{gon} =	16	Ω		150 °C	

figure 10. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

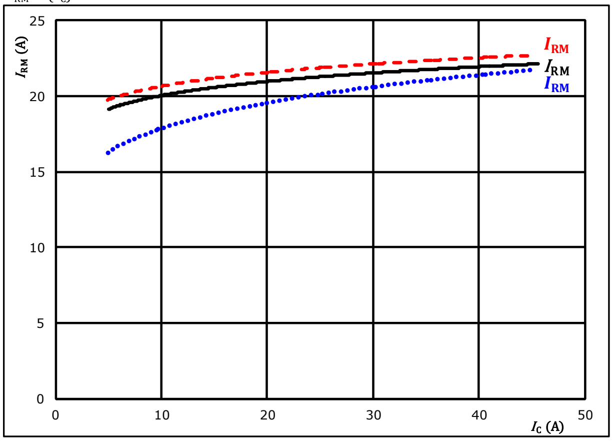


At					
V_{CE} =	600	V		25 °C	
V_{GE} =	±15	V	T_j:	125 °C	
I_C =	25	A		150 °C	

figure 11. **FWD**

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

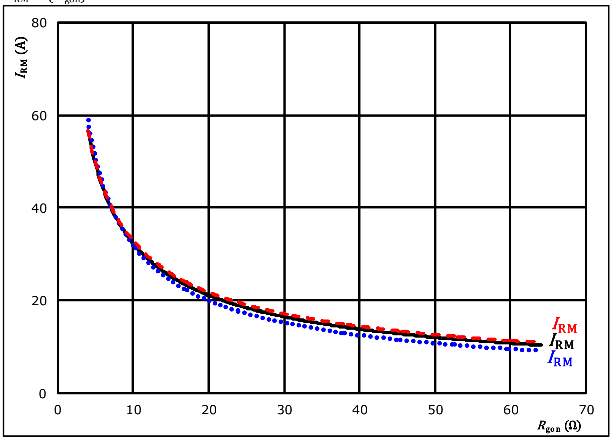


At					
V_{CE} =	600	V		25 °C	
V_{GE} =	±15	V	T_j:	125 °C	
R_{gon} =	16	Ω		150 °C	

figure 12. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



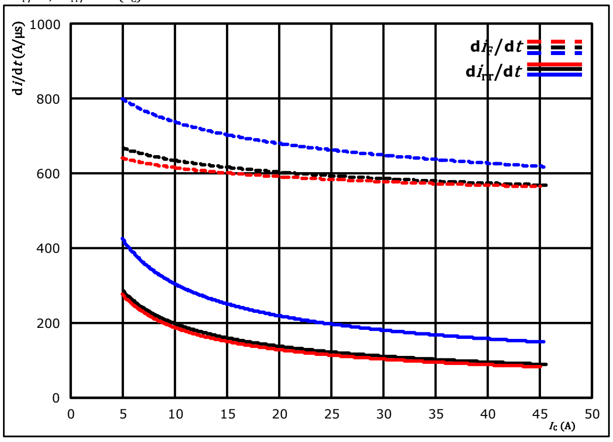
At					
V_{CE} =	600	V		25 °C	
V_{GE} =	±15	V	T_j:	125 °C	
I_C =	25	A		150 °C	

Inverter Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt,\ di_{rr}/dt = f(I_C)$

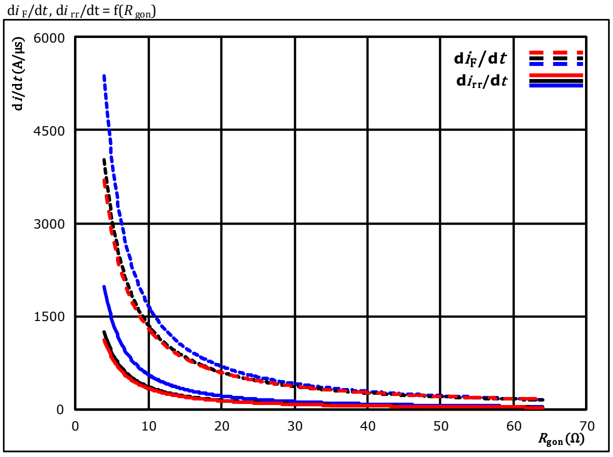


At					
V_{CE} =	600	V	T_j:	25	°C
V_{GE} =	±15	V		125	°C
R_{gon} =	16	Ω		150	°C

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$di_F/dt,\ di_{rr}/dt = f(R_{gon})$

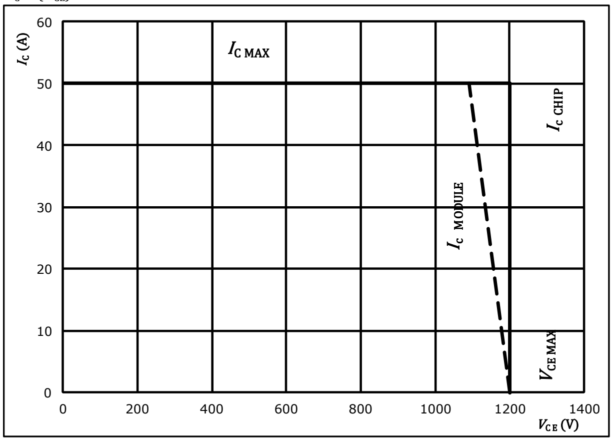


At					
V_{CE} =	600	V	T_j:	25	°C
V_{GE} =	±15	V		125	°C
I_C =	25	A		150	°C

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At		
T_j =	125	°C
R_{gon} =	16	Ω
R_{goff} =	16	Ω

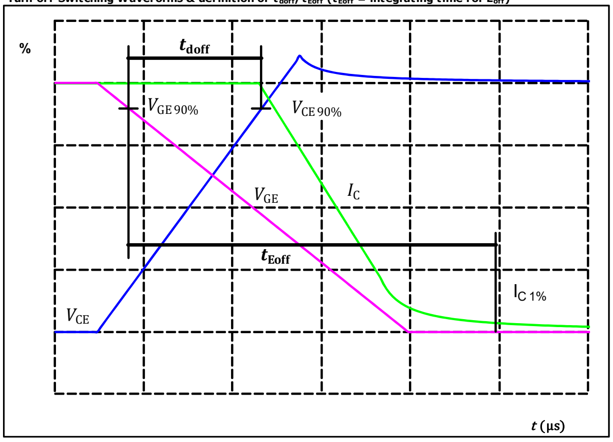
Inverter Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	16 Ω
R_{goff}	=	16 Ω

figure 1. IGBT

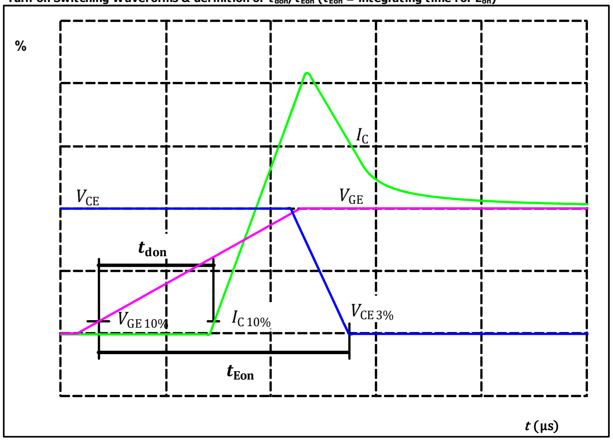
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



V_{GE}(0%) =	-15	V
V_{GE}(100%) =	15	V
V_C(100%) =	600	V
I_C(100%) =	25	A
t_{doff} =	191	ns

figure 2. IGBT

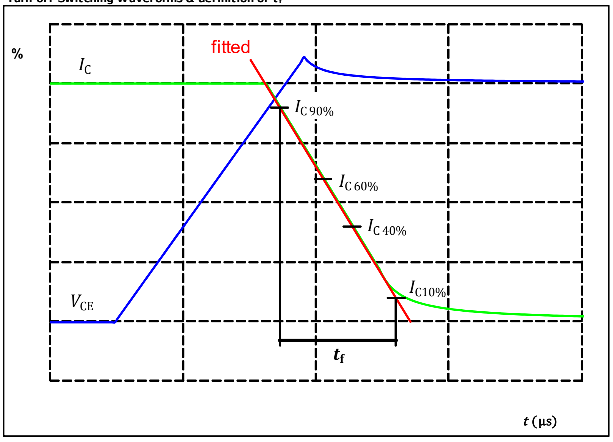
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



V_{GE}(0%) =	-15	V
V_{GE}(100%) =	15	V
V_C(100%) =	600	V
I_C(100%) =	25	A
t_{don} =	149	ns

figure 3. IGBT

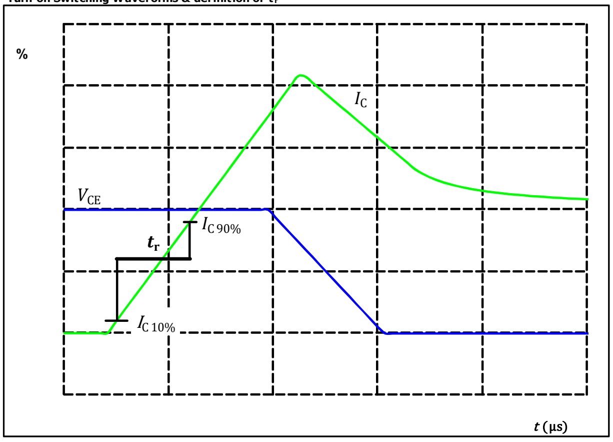
Turn-off Switching Waveforms & definition of t_f



V_C(100%) =	600	V
I_C(100%) =	25	A
t_f =	110	ns

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

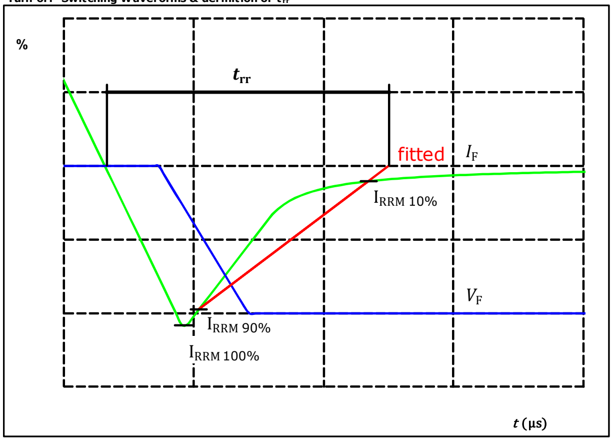


V_C(100%) =	600	V
I_C(100%) =	25	A
t_r =	33	ns

Inverter Switching Characteristics

figure 5. **FWD**

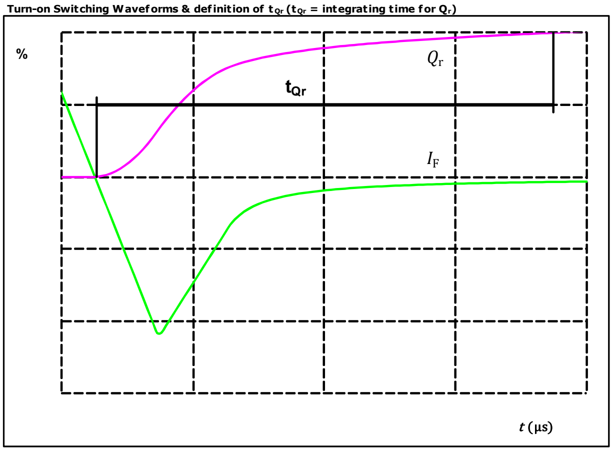
Turn-off Switching Waveforms & definition of t_{rr}



V_F (100%) =	600	V
I_F (100%) =	25	A
I_{RRM} (100%) =	23	A
t_{rr} =	367	ns

figure 6. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



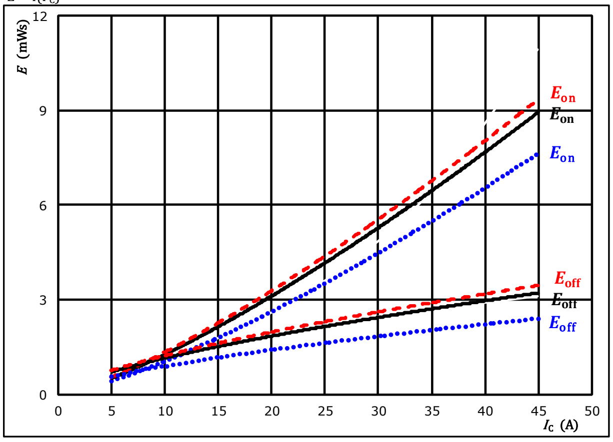
I_F (100%) =	25	A
Q_r (100%) =	3,88	µC

Brake Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



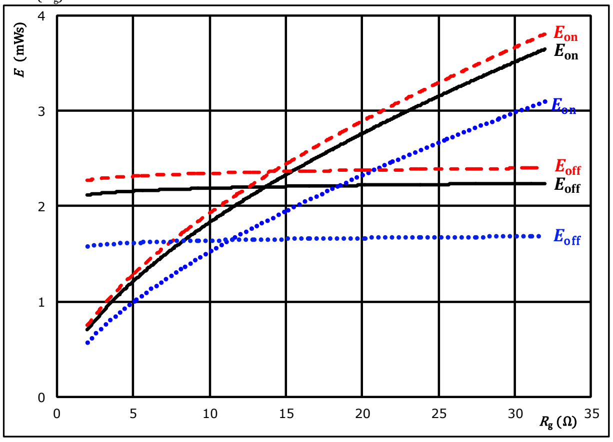
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
R_{gon} =	32	Ω		150 °C	dashed
R_{goff} =	32	Ω			

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



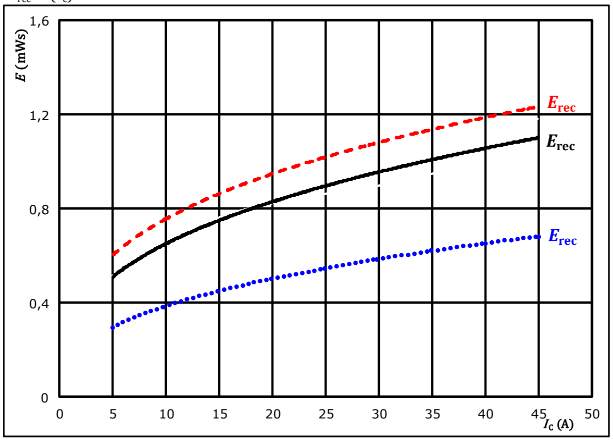
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
I_C =	25	A		150 °C	dashed

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_c)$



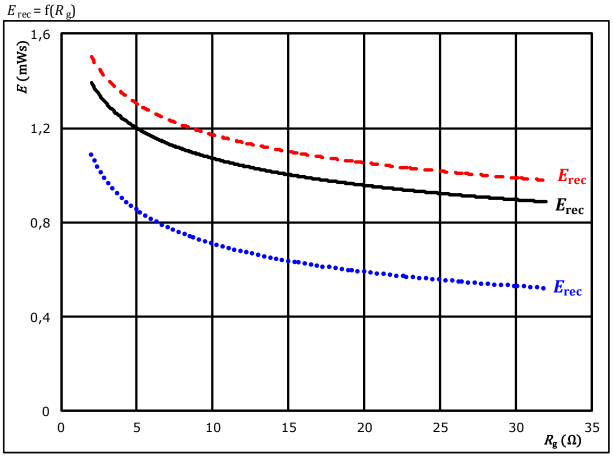
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
R_{gon} =	32	Ω		150 °C	dashed

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

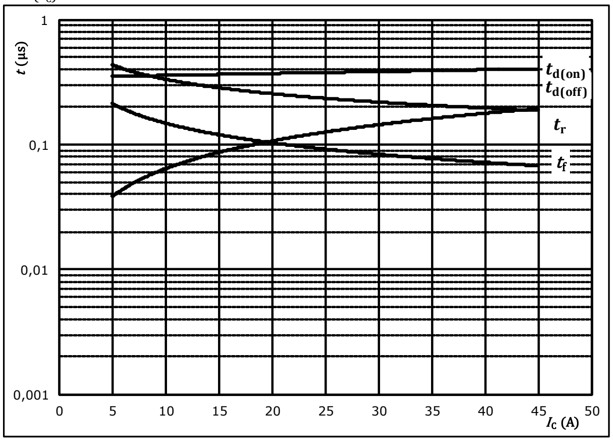
V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
I_C =	25	A		150 °C	dashed

Brake Switching Characteristics

figure 5. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



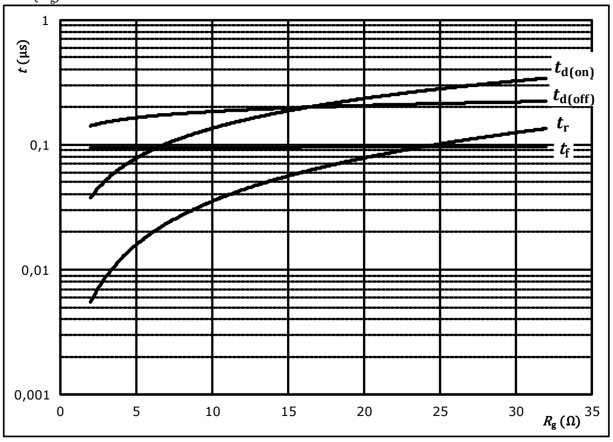
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

figure 6. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



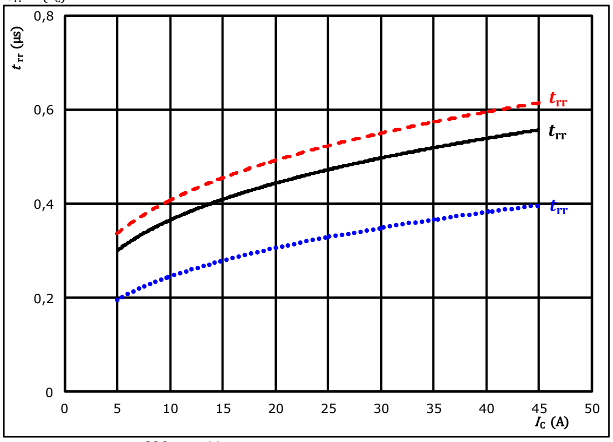
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

figure 7. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

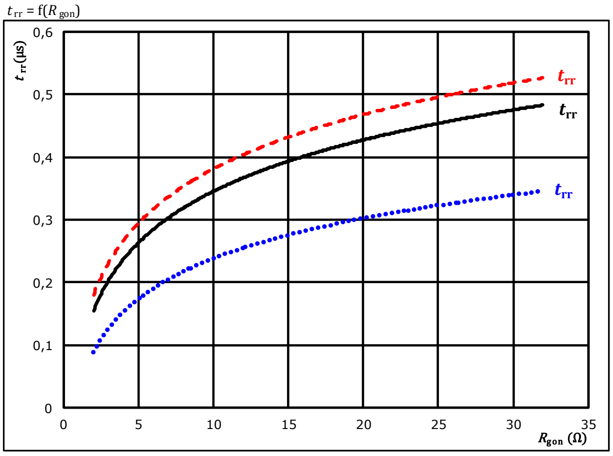


At	V_{CE} =	600	V		25 °C	dotted (blue)
	V_{GE} =	±15	V	T_j:	125 °C	solid (black)
	R_{gon} =	32	Ω		150 °C	dashed (red)

figure 8. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



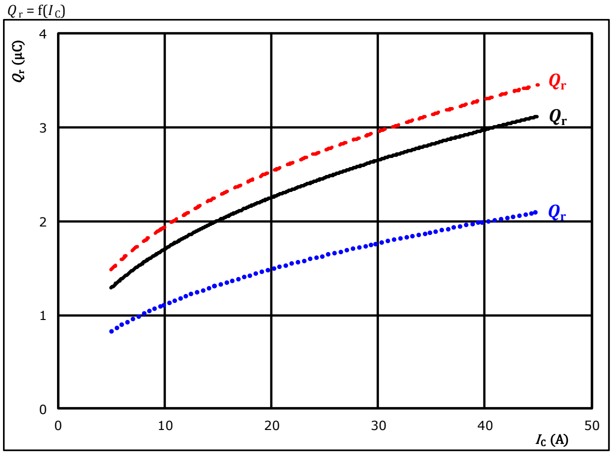
At	V_{CE} =	600	V		25 °C	dotted (blue)
	V_{GE} =	±15	V	T_j:	125 °C	solid (black)
	I_C =	25	A		150 °C	dashed (red)

Brake Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

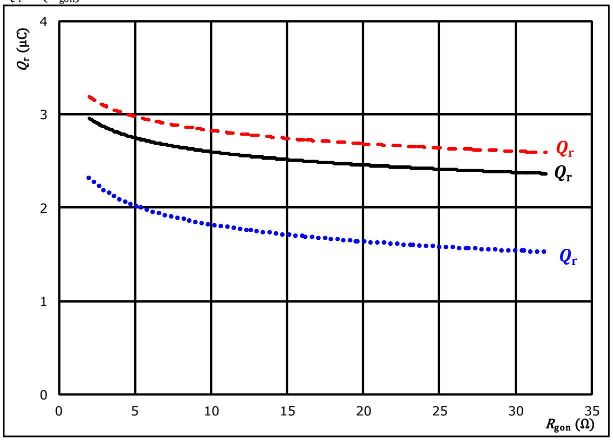


At					
V_{CE} =	600	V		25 °C	············
V_{GE} =	±15	V	T_j:	125 °C	———
R_{gon} =	32	Ω		150 °C	– – –

figure 10. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

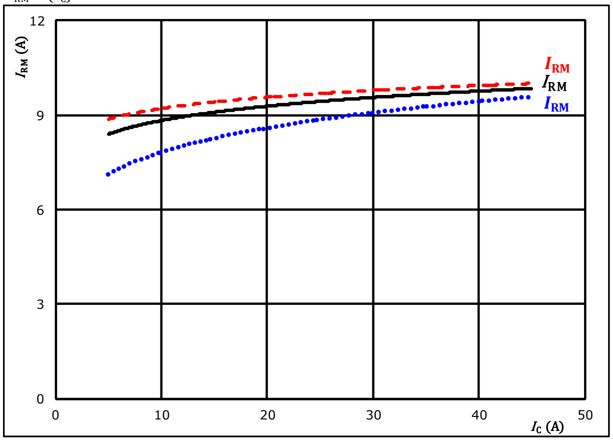


At					
V_{CE} =	600	V		25 °C	············
V_{GE} =	±15	V	T_j:	125 °C	———
I_C =	25	A		150 °C	– – –

figure 11. **FWD**

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

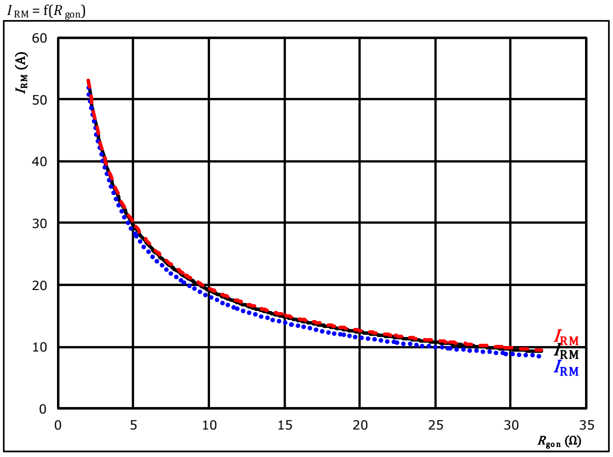


At					
V_{CE} =	600	V		25 °C	············
V_{GE} =	±15	V	T_j:	125 °C	———
R_{gon} =	32	Ω		150 °C	– – –

figure 12. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



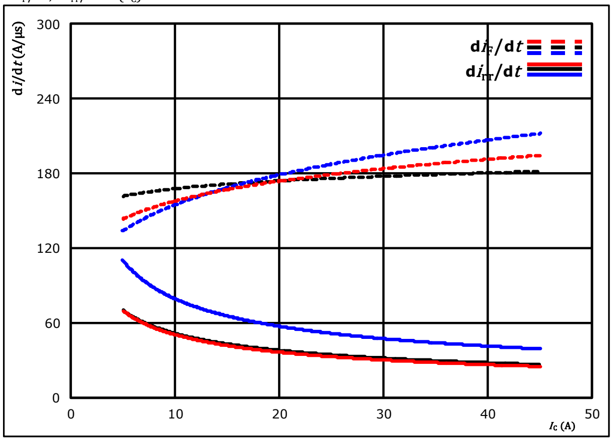
At					
V_{CE} =	600	V		25 °C	············
V_{GE} =	±15	V	T_j:	125 °C	———
I_C =	25	A		150 °C	– – –

Brake Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)

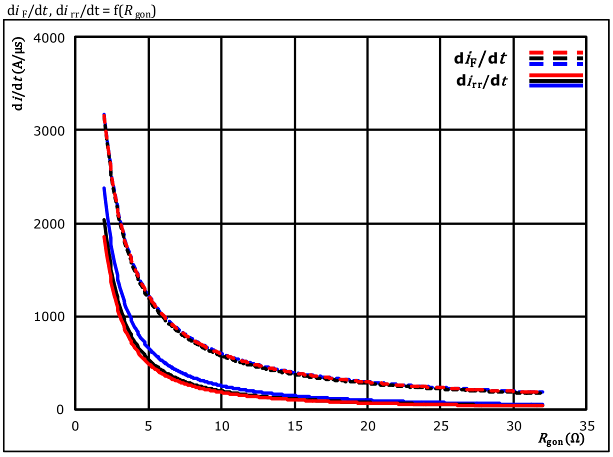


At						
V_{CE} =	600	V		25 °C	....
V_{GE} =	±15	V	T_j:	125 °C	———
R_{gon} =	32	Ω		150 °C	— — —

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

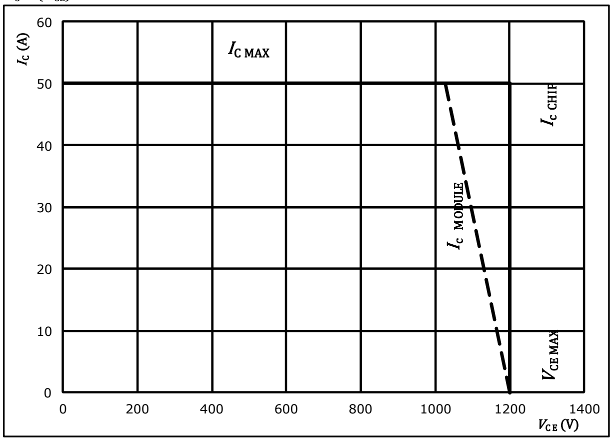


At						
V_{CE} =	600	V		25 °C	....
V_{GE} =	±15	V	T_j:	125 °C	———
I_C=	25	A		150 °C	— — —

figure 15. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



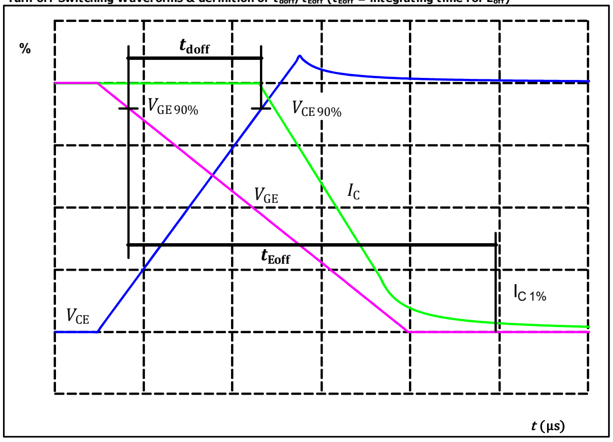
At		
T_j =	125	°C
R_{gon} =	32	Ω
R_{goff} =	32	Ω

Brake Switching Definitions

General conditions		
T_j	=	125 °C
R_{gon}	=	32 Ω
R_{goff}	=	32 Ω

figure 1. IGBT

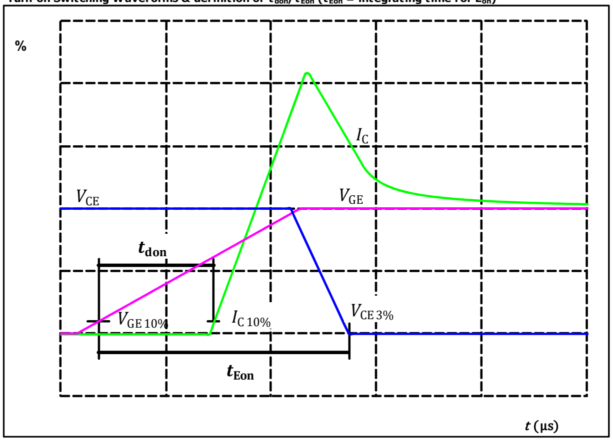
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



V_{GE}(0%) =	-15	V
V_{GE}(100%) =	15	V
V_C(100%) =	600	V
I_C(100%) =	25	A
t_{doff} =	233	ns

figure 2. IGBT

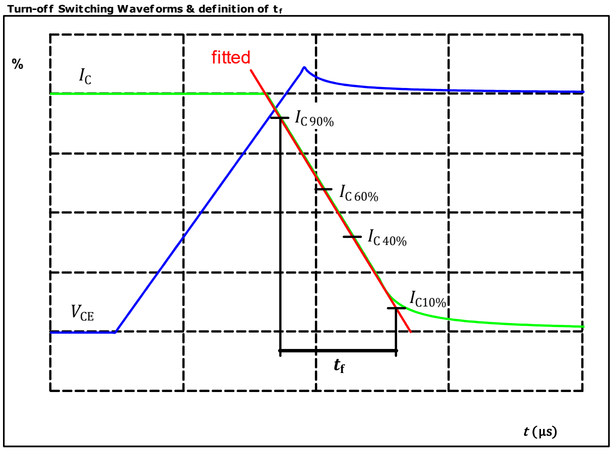
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



V_{GE}(0%) =	-15	V
V_{GE}(100%) =	15	V
V_C(100%) =	600	V
I_C(100%) =	25	A
t_{don} =	389	ns

figure 3. IGBT

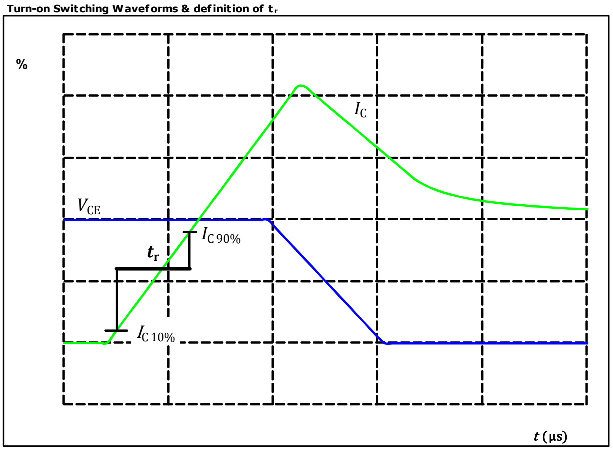
Turn-off Switching Waveforms & definition of t_f



V_C(100%) =	600	V
I_C(100%) =	25	A
t_f =	93	ns

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

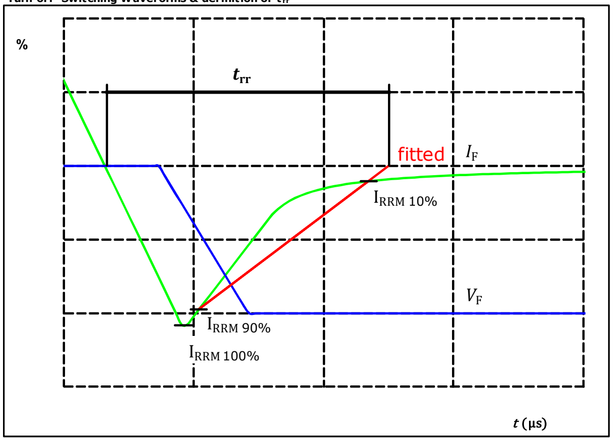


V_C(100%) =	600	V
I_C(100%) =	25	A
t_r =	117	ns

Brake Switching Characteristics

figure 5. **FWD**

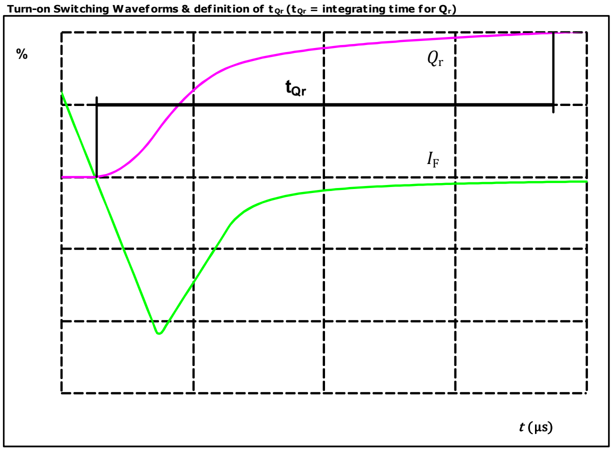
Turn-off Switching Waveforms & definition of t_{rr}



V_F (100%) =	600	V
I_F (100%) =	25	A
I_{RRM} (100%) =	10	A
t_{rr} =	448	ns

figure 6. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	25	A
Q_r (100%) =	2,34	µC

10-EY12PMA025M7-L187A78T
10-E212PMA025M7-L187A78Z
datasheet

Vincotech

Ordering Code & Marking

Version	Ordering Code
without thermal paste 12 mm housing with press-fit pins	10-EY12PMA025M7-L187A78T
with thermal paste 12 mm housing with press-fit pins	10-EY12PMA025M7-L187A78T-/3/
without thermal paste 12 mm housing with Solder pins	10-E212PMA025M7-L187A78Z
with thermal paste 12 mm housing with Solder pins	10-E212PMA025M7-L187A78Z-/3/

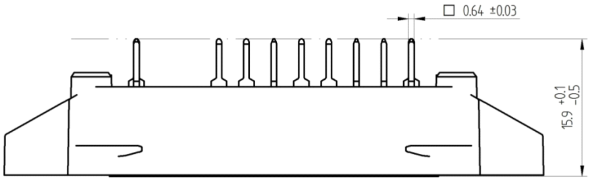
Text	Name		Date code	UL & VIN	Lot	Serial
	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	Type&Ver	Lot number	Serial	Date code		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

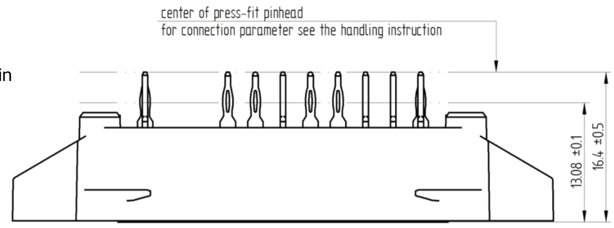
Pin table

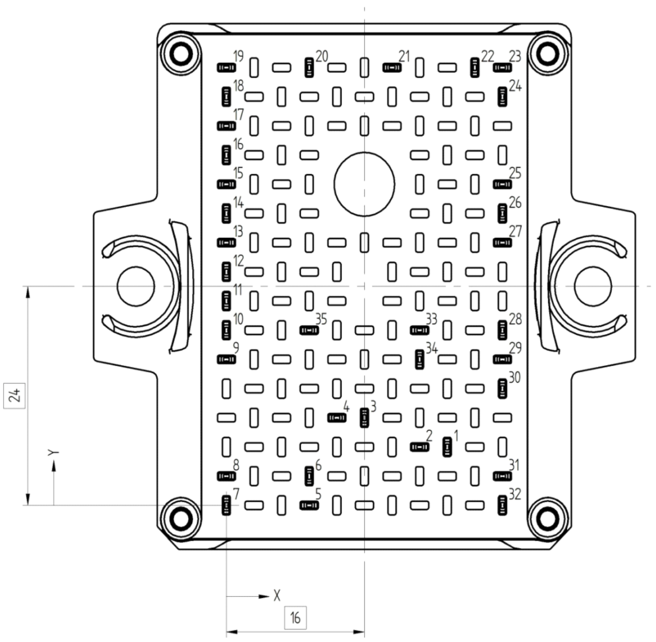
Pin	X	Y	Function
1	25,6	6,4	ACIn2
2	22,4	6,4	ACIn2
3	16	9,6	ACIn1
4	12,8	9,6	ACIn1
5	9,6	0	DC+Rect
6	9,6	3,2	DC+Rect
7	0	0	DC-Rect
8	0	3,2	DC-Rect
9	0	16	G27
10	0	19,2	DC-Br
11	0	22,4	G11
12	0	25,6	DC-1
13	0	28,8	DC-1
14	0	32	G13
15	0	35,2	DC-2
16	0	38,4	DC-2
17	0	41,6	G15
18	0	44,8	DC-3
19	0	48	DC-3
20	9,6	48	Therm1
21	19,2	48	Therm2
22	28,8	48	G16
23	32	48	Ph3
24	32	44,8	Ph3
25	32	35,2	G14
26	32	32	Ph2
27	32	28,8	Ph2
28	32	19,2	G12
29	32	16	Ph1
30	32	12,8	Ph1
31	32	3,2	ACIn3
32	32	0	ACIn3
33	22,4	19,2	DC+Inv
34	22,4	16	DC+Inv
35	9,6	19,2	Br

Solder pin



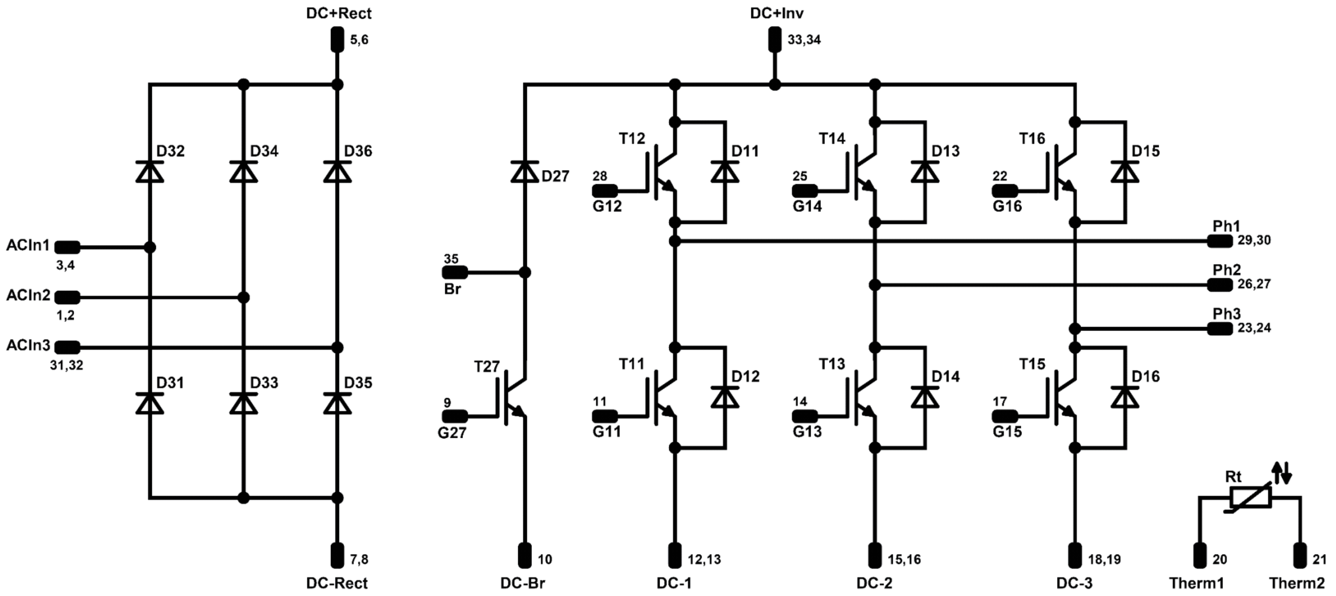
Press-fit pin





Tolerance of pinpositions: ±0,4mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	25 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	25 A	Inverter Diode	
T27	IGBT	1200 V	25 A	Brake Switch	
D27	FWD	1200 V	10 A	Brake Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	45 A	Rectifier Diode	
Rt	NTC			Thermistor	

10-EY12PMA025M7-L187A78T
10-E212PMA025M7-L187A78Z
datasheet

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E2 packages see vincotech.com website.

Package data
Package data for *flow* E2 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-Ex12PMA025M7-L187A78x-D4-14	30 May. 2019	Correction of I_c/I_f values Outline updated	1,2 28